

ABSTRACT

In a cleaning step of a substrate-processing device,
vacuum drawing is made for the space between an inner
5 chamber and an outer chamber that receives the inner chamber.
Temperature of the inner chamber is set higher than the
temperature of the inner chamber during substrate processing
and set lower than the temperature of a substrate support
member. After that, a cleaning gas containing
10 hexafluoroacetylaceton (Hhfac) is supplied in the inner
chamber, and substances to be cleaned off adhering inside
the inner chamber are removed.